

SINGLE METAL PIXEL ARRAY FOR LIGHT VALVE
UTILIZING LATERAL SUBLITHOGRAPHIC SPACER ISOLATION

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BACKGROUND OF THE INVENTION

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1. FIELD OF THE INVENTION

The present invention relates to light valves, and in particular, to pixel cell arrays for light valves which utilize sublithographic isolation based upon the formation of dielectric spacer structures.

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2. DESCRIPTION OF THE RELATED ART

Liquid crystal displays (LCDs) are becoming increasingly prevalent in high-density projection display devices. These display devices typically include a light source which passes light through a light valve.

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One of the methods for producing colors in a liquid crystal display is to sequentially project light having a wavelength corresponding to a primary color onto a single light valve. Color sequential light valves create a spectrum of color within the range of the human perception by switching between a set of discrete primary colors. Typically, red, green, and blue are the primary tri-stimulus colors used to create the remaining colors of the spectrum.

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Specifically, during projection of each primary color, the light intensity is modulated such that combination of the intensities of the primary colors in sequence produces the desired color. The frequency of switching between the primary wavelengths by the light valve should be sufficiently

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rapid to render discrete primary states indistinguishable to the human eye.

Two factors dictate the minimum frequency ^{minimum frequency factors} necessary for switching. The first factor is the ability of the human eye to detect the discrete ^{① detection of colors} primary colors (e.g., red, green, blue). At slower than ideal switching speeds, the human eye will detect a flicker and the primaries may not blend.

The second factor determining the frequency of ^{② video refresh rate} switching is the video refresh rate. During display of video images, the individual frames must be refreshed at frequencies undetectable to the human eye.

The net frequency of switching demanded by the combination of sequential color blending and video refreshing is beyond the capabilities of light valves that utilize thick ($> 1\mu\text{m}$) liquid crystal (LC) transducers. However, thin ($< 1\mu\text{m}$) liquid crystal transducers have been successfully fabricated. These thin LC transducers demonstrate adequate color sequential blending at video refresh rates. One example of such a thin LC transducer pixel cell structure is disclosed in US Patent No. 5,706,067, to Colgan et al.

In general, the conventional thin LC transducer pixel cells possess enhanced responsiveness due to the decreased volume of liquid crystal material between the top and bottom plates. A smaller volume enables the liquid crystal to shift orientation more quickly and in response to a lower applied voltage.

FIG. 1 shows a cross-sectional view of adjacent thin LC transducer pixel cells in a conventional light valve. Light valve portion 100 comprises adjacent pixel cells 110a and 110b having liquid

crystal (LC) material 111 sandwiched within gap 106 between a top plate and a bottom plate. Top plate 102 is composed of a translucent material, typically glass. The bottom plate is formed by the reflective metal pixel electrodes 112a and 112b of adjacent pixels 110a and 110b, respectively.

Pixel electrodes 112a and 112b are separated and electrically isolated by trench 118. Pixel electrodes 112a and 112b lie on top of an upper intermetal dielectric layer 128 that is one component of interconnect scheme 104. Interconnect 104 overlies capacitor structures 118a and 118b formed within underlying silicon substrate 105. Underlying capacitors 118a and 118b are in electrical communication with pixel electrodes 112a and 112b, respectively, through metal-filled vias 140 and middle interconnect metallization layer 124 and lower interconnect metallization layer 122.

FIGS. 2AA-2DB illustrate the steps of the conventional process for forming an array of pixel cells in a light valve. For purposes of convention, all FIGS. 2_A illustrate a top view of the pixel cell, all FIGS. 2_B illustrate a cross-sectional view of the pixel cell along line A-A' of the FIG. 2_A.

FIGS. 2AA-2AB illustrate the starting point for the conventional process for fabricating a thin LC transducer pixel cell. Starting structure 200 is created by forming an upper intermetal dielectric layer 212 over a lower interconnect metallization layer 214. A central portion of upper intermetal dielectric layer 212 is then etched to form via 216. A liner (not shown) typically composed of a Ti/TiN layer combination, is then formed on the walls of via 216, and via 216 is filled with metal (typically CVD

Tungsten). Excess metal is then removed from the surface of upper dielectric layer 212, typically by a combination of etching and chemical-mechanical polishing (CMP).

5 FIGS. 2BA-2BB illustrate formation of the metal pixel electrode in accordance with the conventional process. Metal pixel electrode layer 206 is formed over the entire surface of the pixel cell.

10 FIGS. 2CA-2CB illustrate patterning of a photoresist mask 207 over pixel electrode layer 206. FIGS. 2DA-2DB show the etching of regions of pixel electrode layer 206 unmasked by photoresist 207, to form a plurality of intersecting trenches 218, followed by stripping of photoresist mask 207.

15 Intersecting trenches 218 in turn define a plurality of discrete pixel cell electrodes 230.

20 Fabrication of the thin LC transducer pixel cell is completed by forming an alignment surface (not shown) for the LC material positioned on top of the pixel electrode. Forming this alignment surface is a two step process. First, a dielectric film (typically polyimide) is deposited on top of the pixel electrode. Second, the dielectric film is scored by a rubbing wheel, which traverses the

25 surface of the pixel cell and gouges the alignment surface in a uniform direction. Liquid crystal material is then placed within the cell, and a top glass plate is secured to the tops of the support pillars.

30 The conventional fabrication process described above in FIGS. 2AA-2DB is adequate to produce functional thin LC transducer pixel cells. However, the conventional process flow suffers from a number of disadvantages.

disadvantages

① One problem is that the step of defining and etching the inter-pixel trenches requires an additional masking step. This masking step carries with it penalties in terms of additional defects and higher cost.

Another problem is that the minimum spacing between adjacent pixels is dictated by the limits of resolution of the photolithographic process employed. This limitation is manifested in the step of patterning the mask to form the trenches in the pixel electrode layer, as shown above in FIG. 2CA-2CB. For example, in a $0.3\mu\text{m}$ linewidth photolithographic technology, the distance across trench 218 of FIGS. 2DA-DB could be no less than $0.3\mu\text{m}$.

The closer together the pixels of the array, the better the array will perform. This is particularly true with respect to minimizing leakage of incident light between pixel electrodes through the interconnect and into the underlying substrate, as there is less inter-pixel spacing to allow the passage of incident light. Close proximity between pixels also reduces unwanted optical artifacts attributable to interruption in the continuous pixel array backplane by topography of inter-pixel isolation structures.

Therefore, there is a need in the art for a process of forming an array of pixel cells where inter-pixel spacing between pixels is not constrained by photolithographic parameters, thereby enabling formation of arrays having greater pixel cell densities and enhanced resolution and clarity.

SUMMARY OF THE INVENTION

5 The present invention provides a process flow
for forming an array of pixel cells that does not
rely upon photolithography to define inter-pixel
isolation. Instead, adjacent pixels of the array are
electrically insulated from one another by dielectric
spacer structures formed by the deposition and
etching of a dielectric layer conforming to raised
features of a sacrificial layer. The thickness of
10 the sidewall spacers is determined by the conditions
under which the dielectric material forming the
spacers is deposited. The deposition rate of
dielectric material can be carefully controlled to
produce spacers having a thickness of substantially
15 less than the minimum line width of a given
photolithography system. In this manner, inter-pixel
isolation in accordance with the present invention
can result in fabrication of pixel arrays having much
greater cell densities than found in conventional
20 arrays.

A process flow for forming a pixel cell array in
accordance with one embodiment of the present
invention comprises the steps of forming a
sacrificial layer on top of an upper intermetal
25 dielectric layer, forming a photoresist mask over the
sacrificial layer in a checkerboard pattern which
includes a plurality of masked squares but which
excludes corners of the masked squares, and etching
unmasked portions of the sacrificial layer to stop on
30 the upper intermetal dielectric layer to leave a
raised portion of the sacrificial layer having a top
and sidewalls. The photoresist mask is removed, and
a first dielectric layer is formed over the upper
intermetal dielectric layer and the top of the

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sacrificial layer, the first dielectric layer conforming to the sidewalls. The first dielectric layer is then etched to remove the first dielectric layer over the upper intermetal dielectric layer while leaving vertical dielectric spacer structures along the sidewalls. The raised portions of the sacrificial layer are then removed to leave the dielectric spacer structures, and a metal layer is formed over the upper intermetal dielectric layer and the dielectric spacer structures. The metal layer is then subjected to chemical-mechanical polishing to form a substantially planar metal electrode surface including intervening dielectric structures.

An apparatus in accordance with one embodiment of the present invention comprises an array of pixel cells arranged in a checkerboard pattern having a first set of squares alternating with a second set of squares, the first set of squares and the second set of squares formed from a first metal layer and lacking corners, and further comprises dielectric spacer structures having a thickness intervening between the first set of squares and the second set of squares.

The features and advantages of the present invention will be understood upon consideration of the following detailed description of the invention and the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows a cross-sectional view of adjacent pixel cells in a conventional light valve.

FIGS. 2AA-2DB show top and cross-sectional views of the conventional process steps for forming an array of pixel cells.

FIG. 3 shows a cross-sectional view of a conventional CMOS gate structure.

FIGS. 4AA-4HB show top and cross-sectional views of the process steps for forming an array of pixel cells in accordance with a first embodiment of the present invention.

FIG. 5 shows a plan view of a photoresist mask in accordance with a first alternative embodiment of the present invention.

FIG. 6 shows a plan view of a photoresist mask in accordance with a second alternative embodiment of the present invention.

FIG. 7 shows a cross-sectional view of a chemical-mechanical polishing step in accordance with an alternative embodiment of the present invention.

DETAILED DESCRIPTION

The increasing reliance upon digital integrated circuit technology has heightened the importance of ensuring that process flows leading to formation of pixel arrays are compatible with those leading to formation of CMOS devices. One characteristic feature of CMOS process flows is formation of dielectric spacer structures on either side of the polysilicon gate.

FIG. 3 shows a cross-sectional view of an exemplary CMOS gate structure. First, gate 300 is formed over single crystal silicon 302 to define a channel region 302a. Gate 300 consists of polysilicon layer 304 overlying gate oxide layer 306.

Lightly-doped drain (LDD) regions 308 are then implanted into single crystal silicon 302, aligned to the edge of gate 300. Dielectric spacer structures 310 are then formed adjacent to gate 300. Spacer

structures 310 are created by forming a dielectric layer that conforms to vertical sidewalls 300a of gate 300, and then carefully etching the dielectric layer to leave only spacer structures 310.

5 Finally, source/drain regions 312 are implanted into single crystal silicon 312, aligned to spacer structures 310. Source/drain regions 312 are linked to channel 302a by LDD regions 308.

10 The length of the gate (L_g) is the defining feature of a CMOS device. In general, the minimum linewidth capability of a given photolithography system thus generally defines L_g . In many photoresist systems, the thickness of the spacers (L_s) is typically substantially less than the gate length.

15 Therefore, the present invention utilizes dielectric spacer structures to accomplish sublithographic electrical isolation of adjacent electrodes of a pixel array. In this process, a sacrificial layer is deposited over an upper
20 intermetal dielectric and then etched to form a checkerboard pattern. A dielectric layer conforming to the underlying surface is deposited and then carefully etched to leave only spacer structures along sidewalls of raised portions of the sacrificial
25 layer.

 The sacrificial layer is then removed, leaving only the dielectric spacer structures above the intermetal dielectric layer. A metal layer is formed over the entire surface, and a thin dielectric layer
30 is formed over the metal layer. The thin dielectric layer and metal layer are subjected to chemical-mechanical polishing, such that exposed tops of the dielectric spacer structures separate and electrically isolate electrodes of adjacent pixel cells.

FIGS. 4AA-4HB illustrate the process steps for forming an array of pixel cells in a light valve in accordance with a first embodiment of the present invention. For purposes of convention, all FIGS. 4A illustrate a top view of the pixel cell array, and all FIGS. 4B illustrate a cross-sectional view of the pixel cell array along line A-A' of the FIG. 4A.

FIGS. 4AA-4AB illustrate the starting point for the process. Upper intermetal dielectric layer 402 is formed over upper interconnect metallization layer 400. Vias 404 are etched through upper intermetal dielectric layer 402 to stop on upper interconnect metallization layer 400. Vias 404 are filled with metal, and excess metal is removed.

FIGS. 4BA-4BB show the next step, wherein sacrificial layer 406 is formed over the entire surface. FIGS. 4CA-4CB show patterning of a photoresist layer, followed by development of the photoresist to form first photoresist mask 410. Sacrificial layer 406 is then etched in unmasked regions.

In FIG. 4CA, photoresist mask 410 is shown in the form of a slightly modified checkerboard, with corners 410a excluded. As described in detail below, exclusion of corners 410a from first mask 410 creates gap 411 having a width Z between adjacent diagonally-situated pixels. Subsequent formation of dielectric material within gap 411 prevents electrical contact between the tips of the diagonally-situated electrodes, thereby ensuring adequate inter-pixel isolation.

FIGS. 4DA-4DB show stripping of photoresist mask 410, followed by formation of dielectric layer 412 over the entire surface, including raised portions of

5 sacrificial layer 406. Dielectric layer 412 conforms closely to the underlying topography, becoming vertical along raised sidewalls 406a of sacrificial layer 406. Careful control over the rate of chemical vapor deposition of dielectric material during this step can result in the formation of spacer walls substantially narrower than the minimum linewidth of a given photolithography system.

10 In order to ensure proper electrical isolation between diagonally-situated pixel electrodes, the combined thickness of the dielectric material formed on opposing sides of gap 411 must be greater than the width Z of gap 411. Assuming an equal rate of deposition on both sides of gap 411, the thickness of dielectric layer 411 must therefore be at least $\frac{1}{2}Z$, and preferably larger.

15 FIGS. 4EA-4EB show anisotropic etching of dielectric layer 412. This etching is carefully controlled, so that dielectric layer 412 is completely removed over the surface of upper intermetal dielectric 402 and vias 404, but remains along sidewalls 406a of raised portions of sacrificial layer 406 as dielectric spacer structures 414. Dielectric spacer structures 414 have a curved upper portion 414a reflecting the shape of dielectric layer 412 as originally deposited.

20 FIGS. 4FA-4FB show the next step in the process flow, wherein sacrificial layer 406 is removed to leave only dielectric spacer structures 414 projecting from upper intermetal dielectric layer 402.

25 Next, in FIG. 4GA-4GB, metal layer 416 is formed over the entire surface, and second dielectric layer 418 is formed over metal layer 416.

FIGS. 4HA-4HB show chemical-mechanical polishing through the second dielectric layer into the metal layer. Chemical-mechanical polishing extends into upper curved portion 414a of dielectric spacer structure 414. The result of this chemical-mechanical polishing is formation of adjacent pixel electrodes 415 electronically isolated by intervening dielectric spacers 414.

Fabrication of the liquid crystal silicon light valve is completed by adding liquid crystal material, and then sealing a translucent top plate over the structure.

The thin LC transducer pixel cell and the process for forming this pixel cell in accordance with the present invention offers a number of important advantages. One advantage is that an array is formed having a high density of pixel cells. Because inter-pixel spacing can be reduced below limits imposed by photolithographic constraints, the present invention permits pixel electrodes to readily be positioned closer together than previously possible given a particular photolithography system. Closer spacing of pixels in turn permits finer resolution of images, and minimizes distortion caused by interruption in the otherwise continuous reflective backplane of the light valve attributable to inter-pixel topography. Closer pixel spacing also helps prevent unwanted leakage of light in the space between pixels.

Co-pending, commonly assigned United States Patent Application S.N. __/__, __, entitled "Double-Metal Pixel Array for Light Valve Utilizing Lateral Sublithographic Spacer Isolation" (hereafter "the Co-pending Application") is hereby incorporated by

reference. The Co-pending Application discloses a pixel array and a process for forming the array that is similar to the present invention. Specifically, a first metal layer is etched according to the checkerboard pattern, and then dielectric spacers are formed on sidewalls of the remaining raised features of the first metal layer. A second metal layer is then formed on top of the entire surface. Chemical-mechanical polishing reveals a pixel array consisting of alternating squares of the first and second metal layers.

The present invention also offers several advantages over the Co-pending Application. Specifically, in the Co-pending Application the thickness of the first metal layer and hence the height of the spacers is dictated by the requirements of the reflective electrode. Thus, the first metal layer may be required to have a certain minimum thickness that in turn limits the minimum spacing between adjacent pixel cells.

By contrast, in the present invention the spacer structures are formed on the sidewalls of a sacrificial layer that is subsequently removed. Therefore, the sacrificial layer may be significantly shorter than the first metal layer of the Co-pending Application, with the spacer structures correspondingly less thick. The reduced inter-pixel spacing of the array permitted by this configuration in turn permits fabrication of arrays having a greater density of pixel cells and enhanced image resolution. Thus, inter-pixel spacing of approximately 0.05 μm can be achieved utilizing the present invention.

Although the invention has been described in connection with one specific preferred embodiment, it must be understood that the invention as claimed should not be unduly limited to this embodiment. Various other modifications and alterations in the structure and process will be apparent to those skilled in the art without departing from the scope of the present invention.

For example, as shown in FIG. 4CA, the photoresist layer forming the first mask may be specifically patterned to exclude corners of the square portions, thereby providing space for dielectric material between diagonally-situated pixels. However, there are several possible alternatives to this step.

FIG. 5 shows a plan view of a photoresist mask in accordance with a first alternative embodiment of the present invention. In FIG. 5, first mask 500 is formed by patterning a photoresist layer in a precise checkerboard pattern, followed by carefully over-exposing the photoresist layer during development. As a result of this calculated over-exposure, corners 500a of first mask 500 are rounded and exclude corner portions 502.

FIG. 6 shows a plan view of a photoresist mask in accordance with a second alternative embodiment of the present invention. The exposure kinetics of a particular photolithography system may require surplus photoresist material in corner regions in order to ensure that gaps are formed between diagonally-situated electrodes. Photoresist layer 600 therefore includes corner portions 602 linked together by tabs 604. Development of the patterned photoresist layer 604 may ultimately eliminate tabs

604 altogether, creating the necessary gaps to form between corners of diagonally-situated pixels.

Composition of the various layers making up the array may be varied to achieve optimum device performance and/or process efficiency. For example, FIGS. 4AA-4HB depict successive formation of first and second dielectric layers. These dielectric layers may be composed of silicon oxide, silicon nitride, or any other conforming dielectric material whose rates of formation and etching can be precisely controlled.

Furthermore, significant advances have recently been reported in creating materials having particularly low dielectric constants. Promising "low-k" dielectric materials include, but are not limited to, fluorosilicate glass (FSG), nanoporous silica, and organic polymers.

The thicknesses of the various layers of the array could also be varied and the array would still remain within the scope of the present invention. Thus, by employing low-k dielectric materials to provide inter-pixel isolation, thickness of the dielectric spacers may be decreased. This is because equivalent electrical isolation may be accomplished utilizing the same volume of dielectric material. Pixel arrays having even greater cell densities, higher resolution, and reduced light leakage between pixels may thus be formed in accordance with the present invention.

Finally, while FIG. 4HA-4HB depict chemical-mechanical polishing through the second dielectric layer into the metal layer to form the array, a number of alternatives to this step also exist.

For example, FIG. 7 shows a cross-sectional view of chemical-mechanical polishing in accordance with an alternative embodiment of the present invention. As shown in FIG. 7, chemical-mechanical polishing of metal layer 700 could stop on lower portions of the second dielectric layer, with remaining dielectric material from second dielectric layer removed by wet etching. The relative size of the remaining metal topography is much exaggerated in FIG. 7, as the actual pixel width would be much greater than illustrated.

The approach shown in FIG. 7 would protect the surface of the electrode from reflectance loss attributable to polishing. This approach would also leave curved upper portions of the dielectric spacers largely intact, permitting even closer spacing between adjacent electrodes.

Another alternative chemical-mechanical polishing approach would be to dispense entirely with the second dielectric layer, with the expectation that chemical-mechanical polishing of the metal layer would not overly degrade its reflectance.

Given the multitude of embodiments described above, it is therefore intended that the following claims define the scope of the present invention, and that the methods and structures within the scope of these claims and their equivalents be covered hereby.